

BCW30LT1G, SBCW30LT1G

General Purpose Transistors

PNP Silicon

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--------------------------------|-----------|-------|------|
| Collector - Emitter Voltage | V_{CEO} | -32 | Vdc |
| Collector - Base Voltage | V_{CBO} | -32 | Vdc |
| Emitter-Base Voltage | V_{EBO} | -5.0 | Vdc |
| Collector Current - Continuous | I_C | -100 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|-----------------|-------------|---------------------------|
| Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 225 | mW |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 556 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 300 | mW |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 417 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

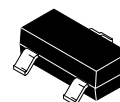
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

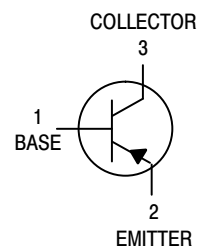


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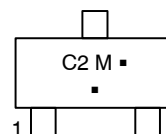
<http://onsemi.com>



SOT-23 (TO-236)
CASE 318-08
STYLE 6



MARKING DIAGRAM



- C2 = Specific Device Code
- M = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping |
|------------|---------------------|-------------------|
| BCW30LT1G | SOT-23 (Pb-Free) | 3,000/Tape & Reel |
| SBCW30LT1G | SOT-23 (Pb-Free) | 3,000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|--|---------------|------|-------------|-------------------------|
| OFF CHARACTERISTICS | | | | |
| Collector-Emitter Breakdown Voltage ($I_C = -2.0\text{ mA}$, $I_E = 0$) | $V_{(BR)CEO}$ | -32 | - | Vdc |
| Collector-Emitter Breakdown Voltage ($I_C = -100\text{ }\mu\text{A}$, $V_{EB} = 0$) | $V_{(BR)CES}$ | -32 | - | Vdc |
| Collector-Base Breakdown Voltage ($I_C = -10\text{ }\mu\text{A}$, $I_C = 0$) | $V_{(BR)CBO}$ | -32 | - | Vdc |
| Emitter-Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{A}$, $I_C = 0$) | $V_{(BR)EBO}$ | -5.0 | - | Vdc |
| Collector Cutoff Current ($V_{CB} = -32\text{ Vdc}$, $I_E = 0$) ($V_{CB} = -32\text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$) | I_{CBO} | - | -100 -10 | nAdc μAdc |
| ON CHARACTERISTICS | | | | |
| DC Current Gain ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$) | h_{FE} | 215 | 500 | - |
| Collector-Emitter Saturation Voltage ($I_C = -10\text{ mA}$, $I_B = -0.5\text{ mA}$) | $V_{CE(sat)}$ | - | -0.3 | Vdc |
| Base-Emitter On Voltage ($I_C = -2.0\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$) | $V_{BE(on)}$ | -0.6 | -0.75 | Vdc |
| SMALL-SIGNAL CHARACTERISTICS | | | | |
| Output Capacitance ($I_E = 0$, $V_{CB} = -10\text{ Vdc}$, $f = 1.0\text{ MHz}$) | C_{obo} | - | 7.0 | pF |
| Noise Figure ($I_C = -0.2\text{ mA}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$) | NF | - | 10 | dB |

TYPICAL NOISE CHARACTERISTICS

($V_{CE} = -5.0\text{ Vdc}$, $T_A = 25^\circ\text{C}$)

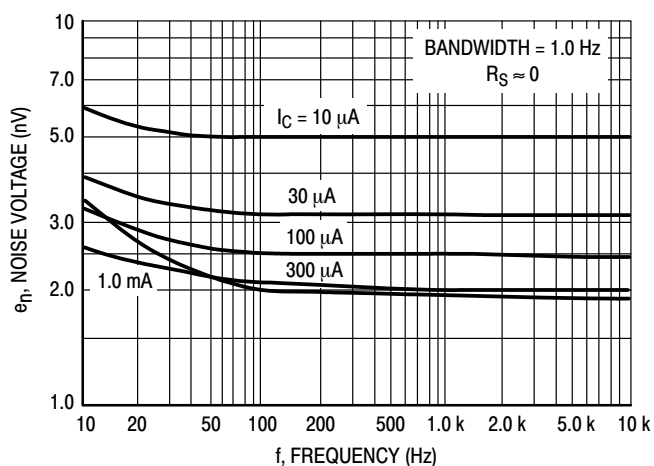


Figure 1. Noise Voltage

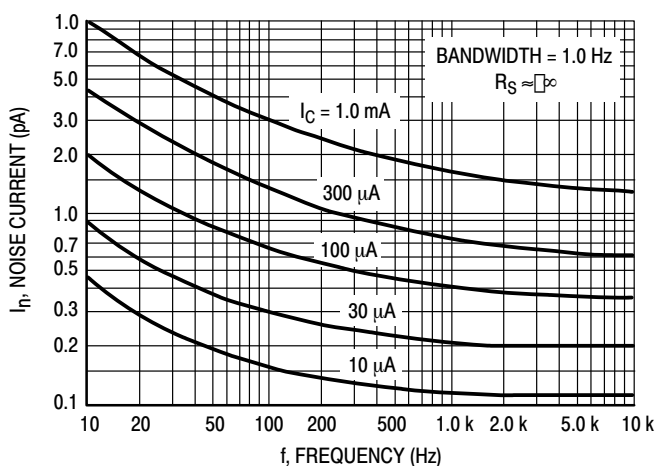


Figure 2. Noise Current

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NOISE FIGURE CONTOURS

($V_{CE} = -5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

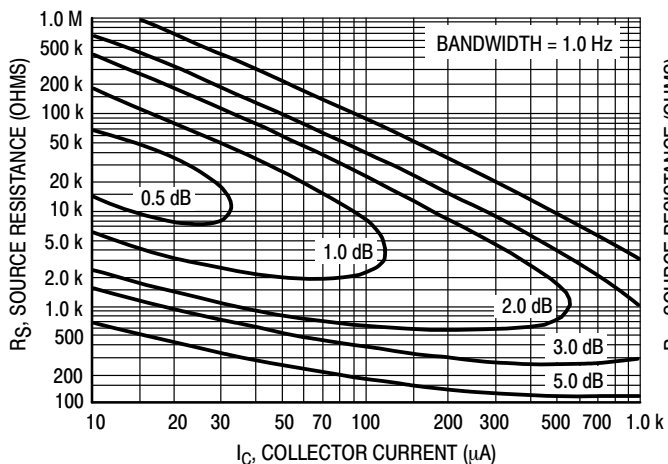


Figure 3. Narrow Band, 100 Hz

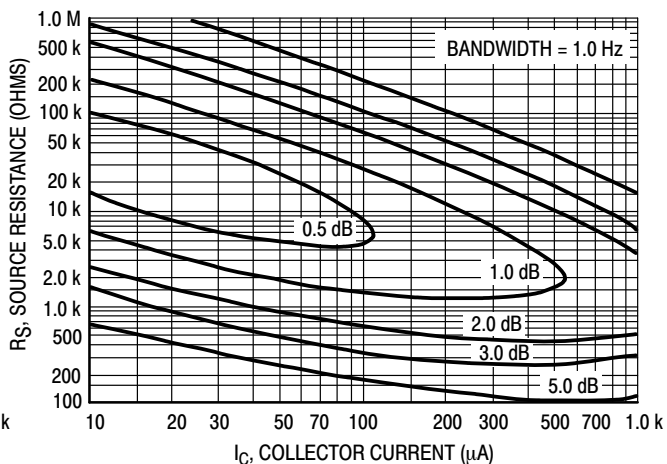


Figure 4. Narrow Band, 1.0 kHz

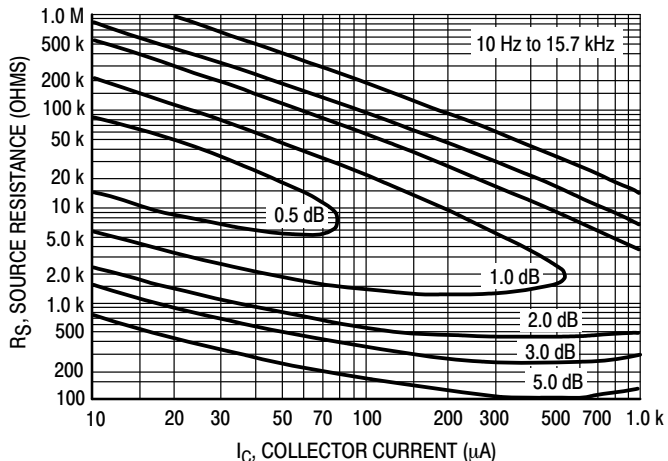


Figure 5. Wideband

Noise Figure is Defined as:

$$NF = 20 \log_{10} \left[\frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right]^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)

I_n = Noise Current of the Transistor referred to the input. (Figure 4)

K = Boltzman's Constant ($1.38 \times 10^{-23} \text{ J/}^\circ\text{K}$)

T = Temperature of the Source Resistance ($^\circ\text{K}$)

R_S = Source Resistance (Ohms)

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TYPICAL STATIC CHARACTERISTICS

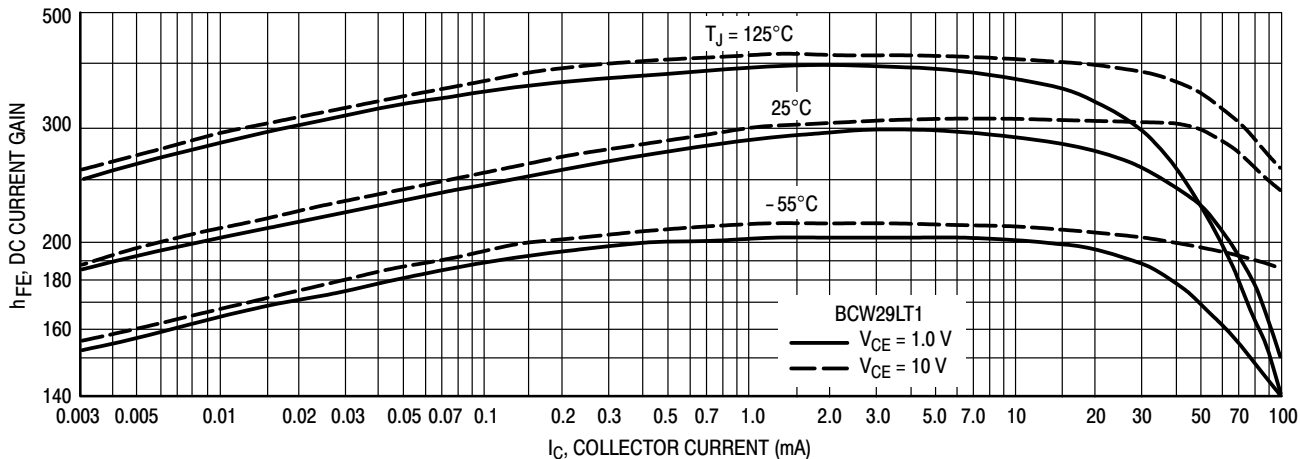


Figure 6. DC Current Gain

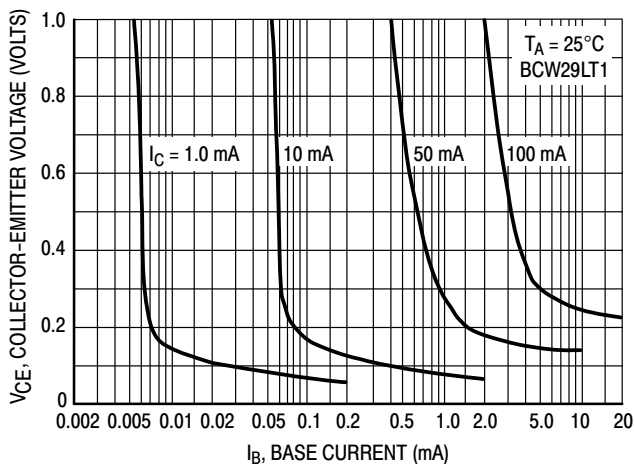


Figure 7. Collector Saturation Region

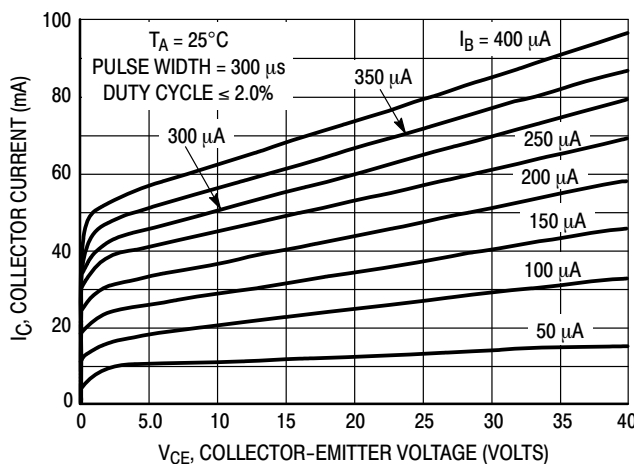


Figure 8. Collector Characteristics

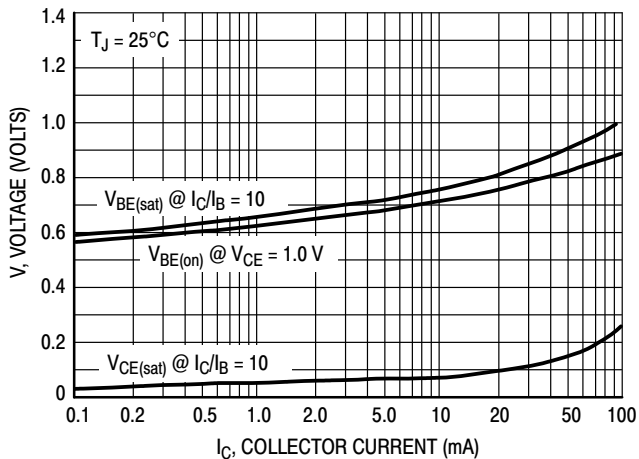


Figure 9. "On" Voltages

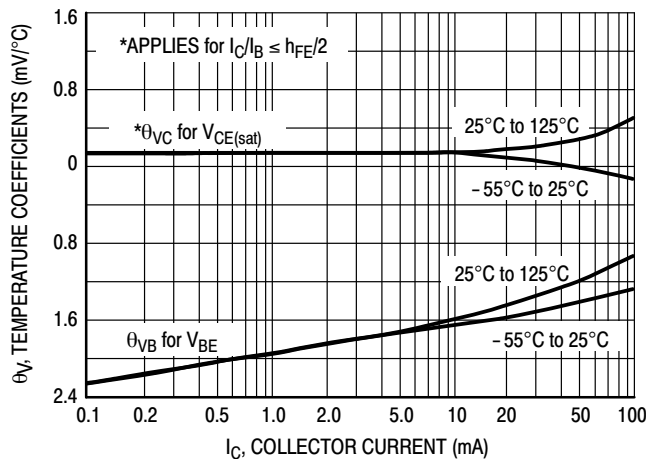


Figure 10. Temperature Coefficients

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TYPICAL DYNAMIC CHARACTERISTICS

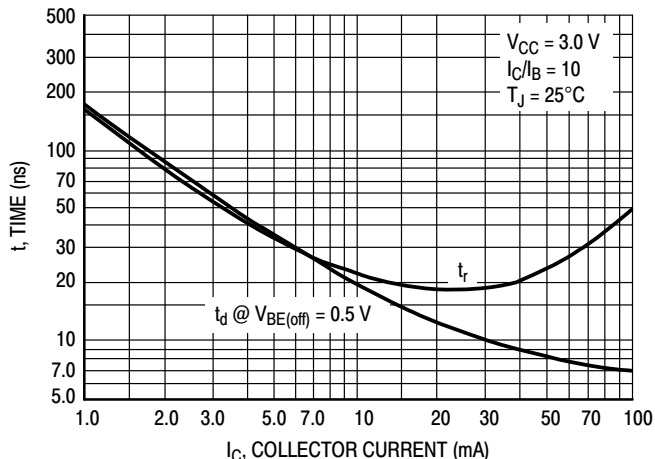


Figure 11. Turn-On Time

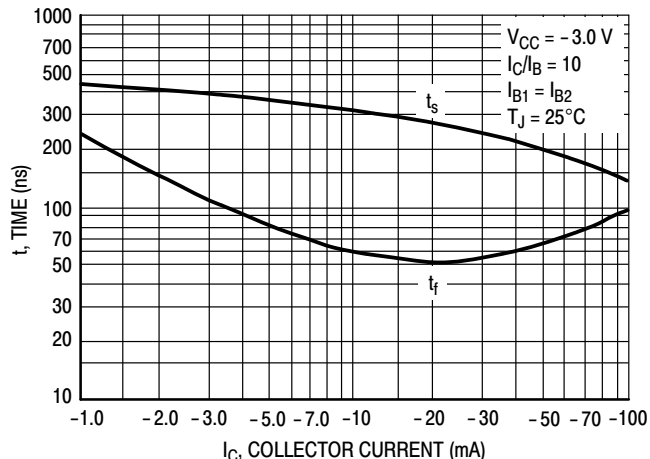


Figure 12. Turn-Off Time

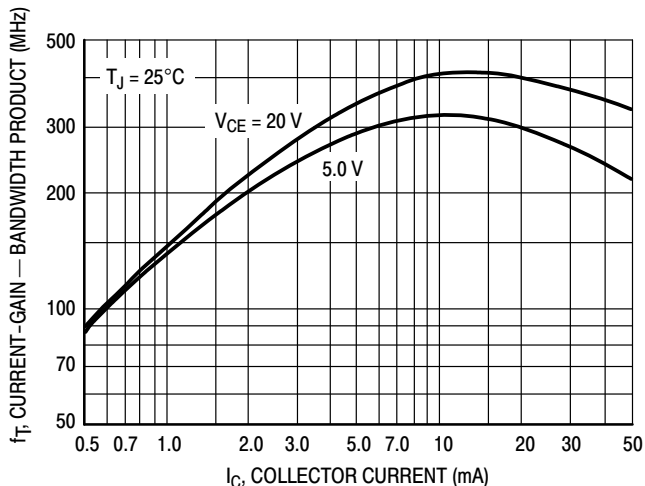


Figure 13. Current-Gain — Bandwidth Product

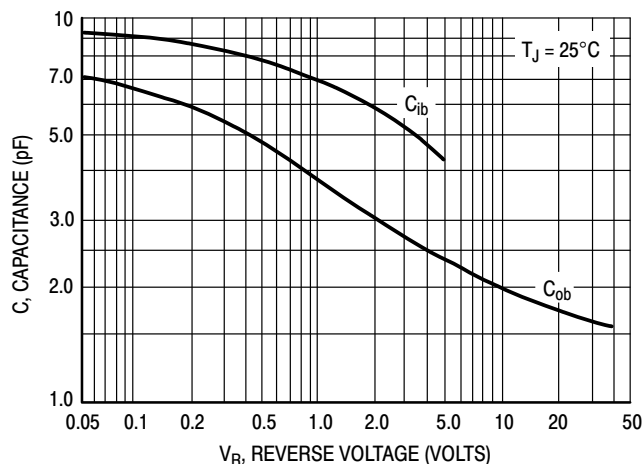


Figure 14. Capacitance

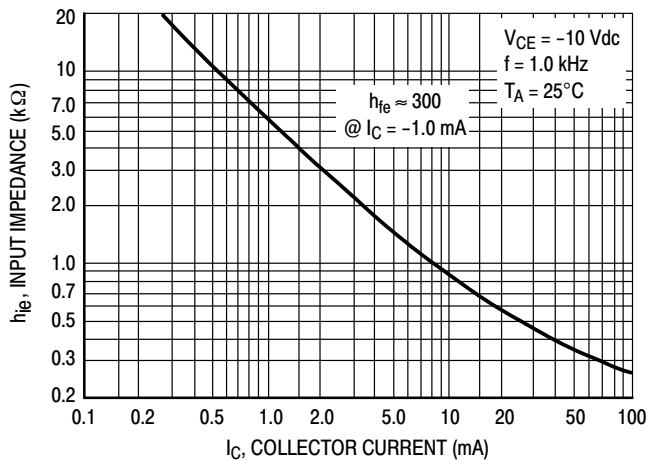


Figure 15. Input Impedance

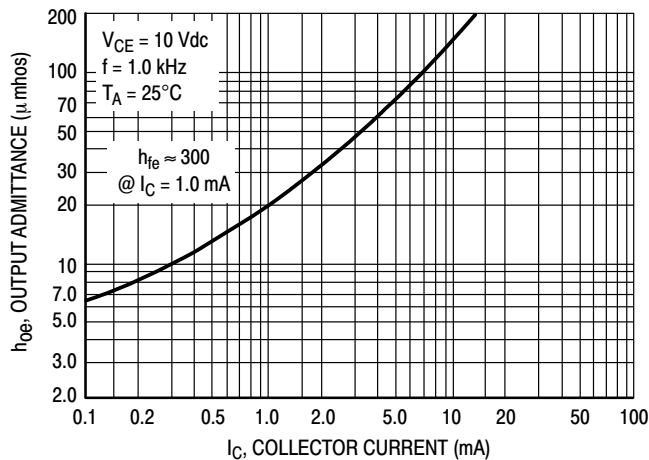


Figure 16. Output Admittance

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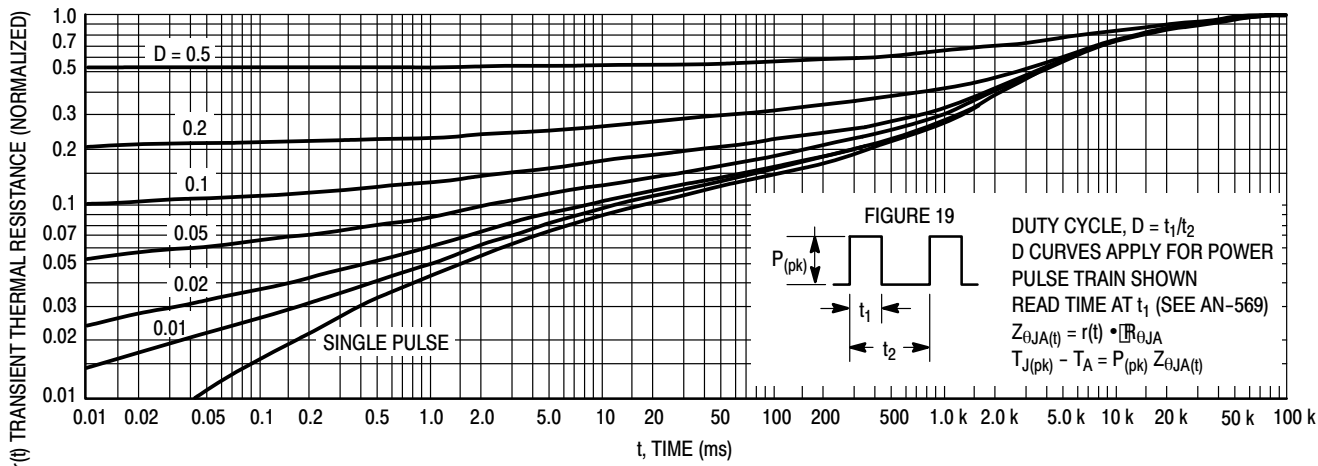


Figure 17. Thermal Response

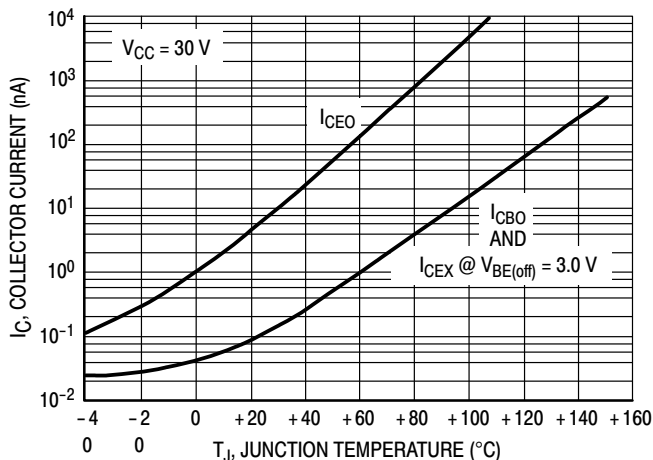


Figure 18. Typical Collector Leakage Current

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 19. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 17 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 17 by the steady state value $R_{\theta JA}$.

Example:

The BCW29LT1 is dissipating 2.0 watts peak under the following conditions:

$$t_1 = 1.0 \text{ ms}, t_2 = 5.0 \text{ ms} (D = 0.2)$$

Using Figure 17 at a pulse width of 1.0 ms and $D = 0.2$, the reading of $r(t)$ is 0.22.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^\circ\text{C}.$$

For more information, see AN-569.

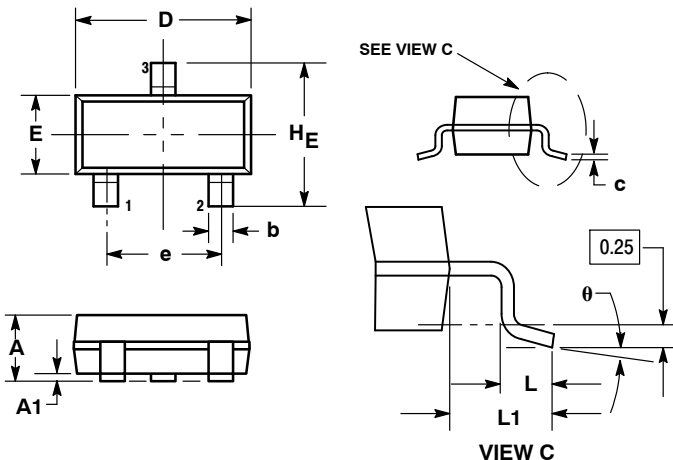
BCW30LT1G, SBCW30LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)

CASE 318-08

ISSUE AP



NOTES:

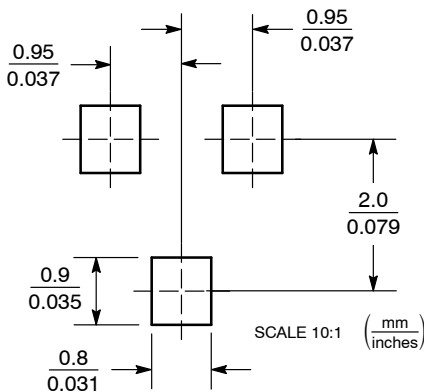
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.040 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.001 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.018 | 0.020 |
| c | 0.09 | 0.13 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.081 |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.029 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| θ | 0° | --- | 10° | 0° | --- | 10° |

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

SOLDERING FOOTPRINT



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- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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